

500.39825X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

T. HIROSE, et al

Serial No.:

09/800,495

Filed:

March 8, 2001

For:

METHOD OF DETECTING AND MEASURING ENDPOINT OF

POLISHING PROCESSING AND ITS APPARATUS AND

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

**USING THE SAME** 

Group:

3723

Examiner:

D. Nguyen

**AMENDMENT** 

Commissioner for Patents Washington, D.C. 20231

July 8, 2002

RECEIVED

JUL-9 2002

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Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated June 6, 2002.

## IN THE CLAIMS:

Please amend claim 1 as follows:

1. (amended) A method of detecting an endpoint of polishing processing,

comprising the steps of:

concurrently irradiating a film formed on a surface of a wafer under polishing processing with light having two or more different wavelengths;

detecting reflected lights from said film caused by the irradiation; and detecting the endpoint of polishing processing of said film on the basis of a relationship between intensities of the detected reflected lights.